

# **CSD18536KTT 60V N-Channel NexFET™ Power MOSFET**

#### 1 Features

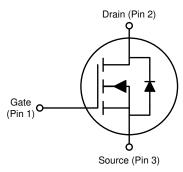
- Ultralow Q<sub>g</sub> and Q<sub>gd</sub>
- Low thermal resistance
- Avalanche rated
- Pb-free terminal plating
- RoHS compliant
- Halogen free
- D<sup>2</sup>PAK plastic package

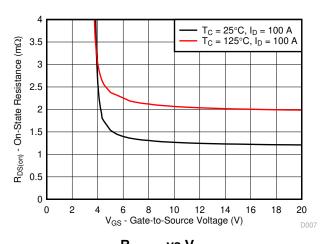
# 2 Applications

- Secondary side synchronous rectifier
- Motor control

# 3 Description

This 60V, 1.3mΩ, D<sup>2</sup>PAK (TO-263) NexFET<sup>™</sup> power MOSFET is designed to minimize losses in power conversion applications.





R<sub>DS(on)</sub> vs V<sub>GS</sub>

#### **Product Summary**

T <sub>A</sub> = 25°	C	TYPICAL VA	UNIT	
V <sub>DS</sub>	Drain-to-Source Voltage 60			
Qg	Gate Charge Total (10V)	108		nC
Q <sub>gd</sub>	Gate Charge Gate-to-Drain	14	nC	
В	Drain-to-Source On-Resistance	V <sub>GS</sub> = 4.5V 1.7		mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 10V 1.3		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.8	V	

### Ordering Information (1)

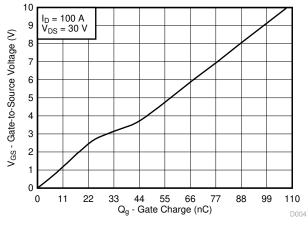
DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18536KTT	500	13-Inch	D <sup>2</sup> PAK Plastic Package	Tape &
CSD18536KTTT	50	Reel	D FAR Flastic Fackage	Reel

For all available packages, see the orderable addendum at the end of the data sheet.

#### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	5°C	VALUE	UNIT
V <sub>DS</sub>	Drain-to-Source Voltage	60	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
	Continuous Drain Current (Package limited)	200	Α
I <sub>D</sub>	Continuous Drain Current (Silicon limited), T <sub>C</sub> = 25°C	349	Α
	Continuous Drain Current (Silicon limited), T <sub>C</sub> = 100°C	247	Α
I <sub>DM</sub>	Pulsed Drain Current (1)	400	Α
P <sub>D</sub>	Power Dissipation	375	W
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to 175	°C
E <sub>AS</sub>	Avalanche Energy, Single Pulse $I_D$ = 128A, L = 0.1mH, $R_G$ = 25 $\Omega$	819	mJ

Max  $R_{\theta JC}$  = 0.4°C/W, pulse duration ≤100µs, duty cycle ≤1%



**Gate Charge** 



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# 4 Specifications

# **4.1 Electrical Characteristics**

(T<sub>A</sub> = 25°C unless otherwise stated)

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
STATIC	CHARACTERISTICS			'	
BV <sub>DSS</sub>	Drain-to-source voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60		V
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 48V		1	μA
I <sub>GSS</sub>	Gate-to-source leakage current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 20V		100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.4 1.8	2.2	V
В	Drain-to-source on-resistance	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 100A	1.7	2.2	mΩ
R <sub>DS(on)</sub>	Drain-to-source on-resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 100A	1.3	1.6	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 6V, I <sub>D</sub> = 100A	312		S
DYNAMI	IC CHARACTERISTICS		1	1	
C <sub>iss</sub>	Input capacitance		8790	11430	pF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0V, V_{DS} = 30V, f = 1MHz$	1410	1840	pF
C <sub>rss</sub>	Reverse transfer capacitance		39	51	pF
R <sub>G</sub>	Series gate resistance		0.7	1.4	Ω
Q <sub>g</sub>	Gate charge total (10V)		108	140	nC
Q <sub>gd</sub>	Gate charge gate-to-drain	V = 20V I = 400A	14		nC
Q <sub>gs</sub>	Gate charge gate-to-source	$V_{DS} = 30V, I_{D} = 100A$	18		nC
Q <sub>g(th)</sub>	Gate charge at V <sub>th</sub>		17		nC
Q <sub>oss</sub>	Output charge	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V	230		nC
t <sub>d(on)</sub>	Turn on delay time		11		ns
t <sub>r</sub>	Rise time	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V,	5		ns
t <sub>d(off)</sub>	Turn off delay time	$I_{DS}$ = 100A, $R_G$ = 0 $\Omega$	24		ns
t <sub>f</sub>	Fall time		4		ns
DIODE C	CHARACTERISTICS	,	1	l	
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 100A, V <sub>GS</sub> = 0V	0.9	1.0	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DS</sub> = 30V, I <sub>F</sub> = 100A,	323		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300A/μs	86		ns

# **4.2 Thermal Information**

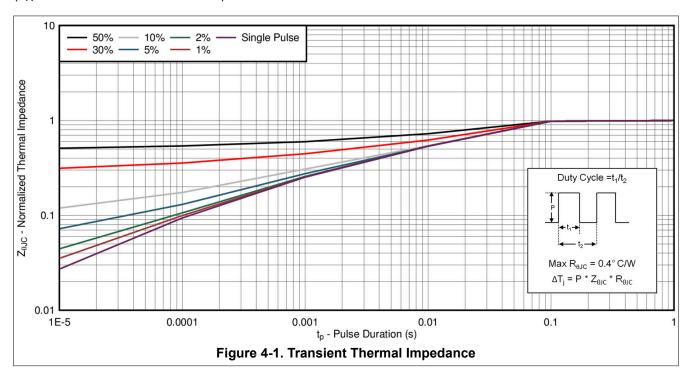
(T<sub>A</sub> = 25°C unless otherwise stated)

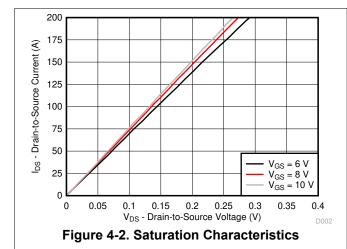
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance			0.4	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance			62	°C/W



# 4.3 Typical MOSFET Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 





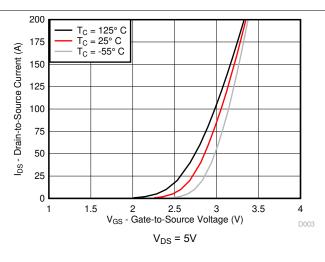
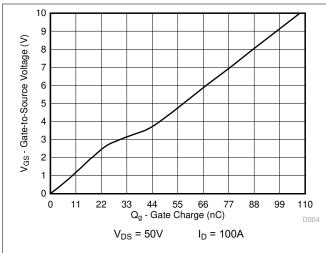


Figure 4-3. Transfer Characteristics



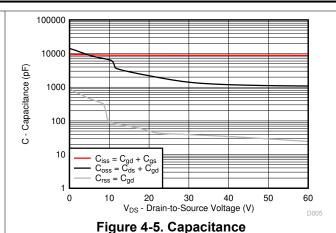
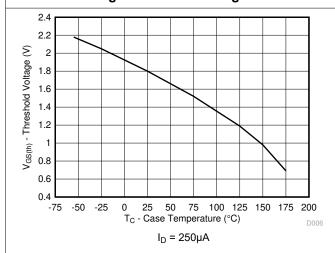


Figure 4-4. Gate Charge



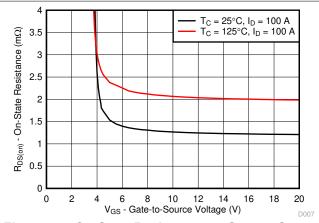


Figure 4-6. Threshold Voltage vs Temperature

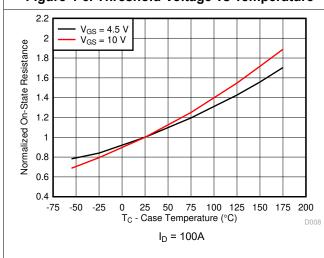


Figure 4-7. On-State Resistance vs Gate-to-Source Voltage

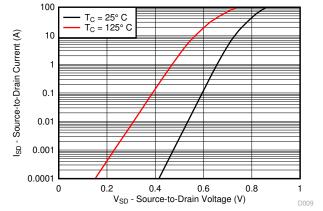
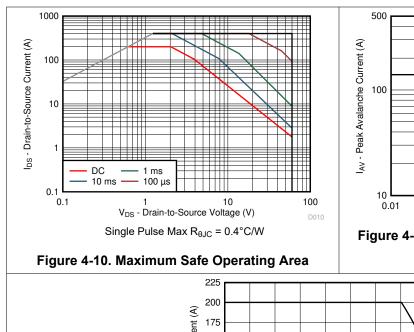


Figure 4-8. Normalized On-State Resistance vs
Temperature

Figure 4-9. Typical Diode Forward Voltage





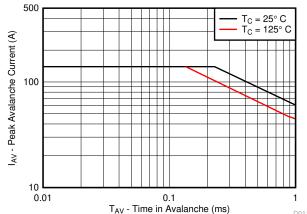


Figure 4-11. Single Pulse Unclamped Inductive Switching

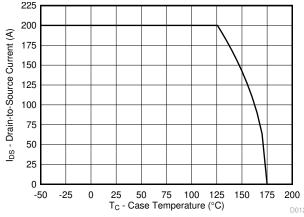


Figure 4-12. Maximum Drain Current vs Temperature

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# 5 Device and Documentation Support

## 5.1 Third-Party Products Disclaimer

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### **5.2 Documentation Support**

#### 5.2.1 Related Documentation

### 5.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 5.4 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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#### 5.5 Trademarks

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#### 5.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 5.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

# **6 Revision History**

#### Changes from Revision \* (March 2016) to Revision A (June 2025)

Page



# 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
CSD18536KTT	Active	Production	DDPAK/ TO-263 (KTT)   2	500   LARGE T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD18536KTT
CSD18536KTT.B	Active	Production	DDPAK/ TO-263 (KTT)   2	500   LARGE T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD18536KTT
CSD18536KTTT	Active	Production	DDPAK/ TO-263 (KTT)   2	50   SMALL T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD18536KTT
CSD18536KTTT.B	Active	Production	DDPAK/ TO-263 (KTT)   2	50   SMALL T&R	ROHS Exempt	SN	Level-2-260C-1 YEAR	-55 to 175	CSD18536KTT

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



# **PACKAGE OPTION ADDENDUM**

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# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

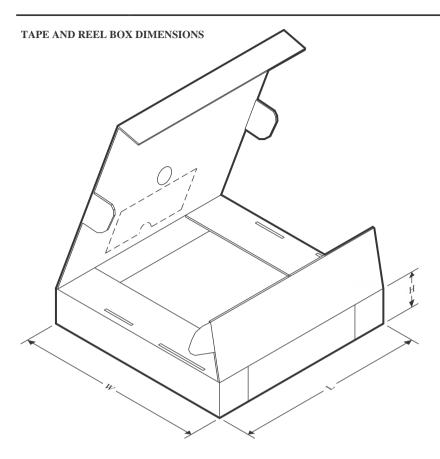


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18536KTT	DDPAK/ TO-263	KTT	2	500	330.0	24.4	10.8	16.3	5.11	16.0	24.0	Q2
CSD18536KTTT	DDPAK/ TO-263	KTT	2	50	330.0	24.4	10.8	16.3	5.11	16.0	24.0	Q2

**PACKAGE MATERIALS INFORMATION** 

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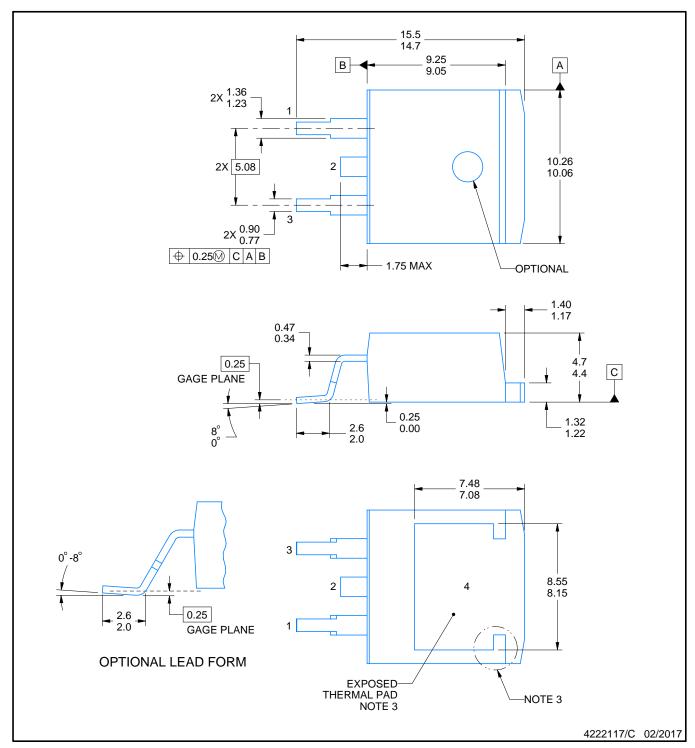


### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18536KTT	DDPAK/TO-263	ктт	2	500	340.0	340.0	38.0
CSD18536KTTT	DDPAK/TO-263	KTT	2	50	340.0	340.0	38.0



TO-263



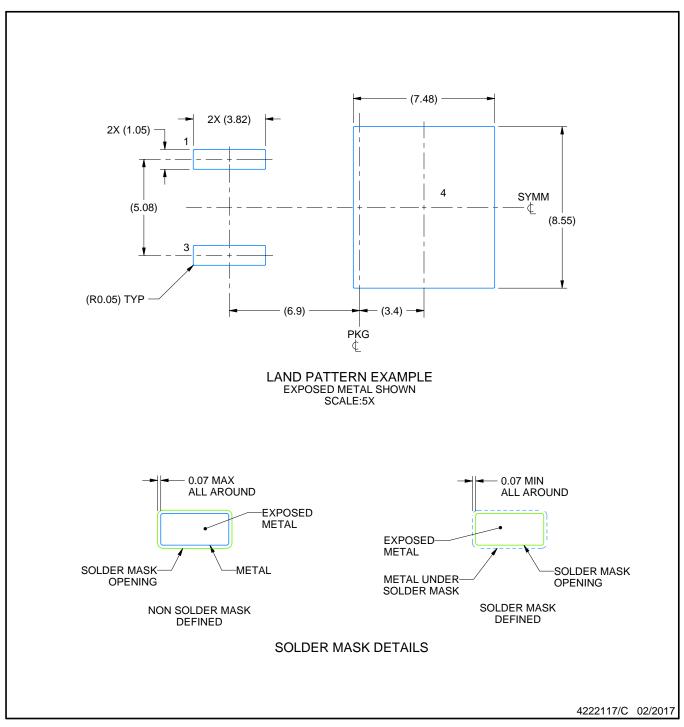
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.
- Features may not exist and shape may vary per different assembly sites.
   Reference JEDEC registration TO-263.



TO-263

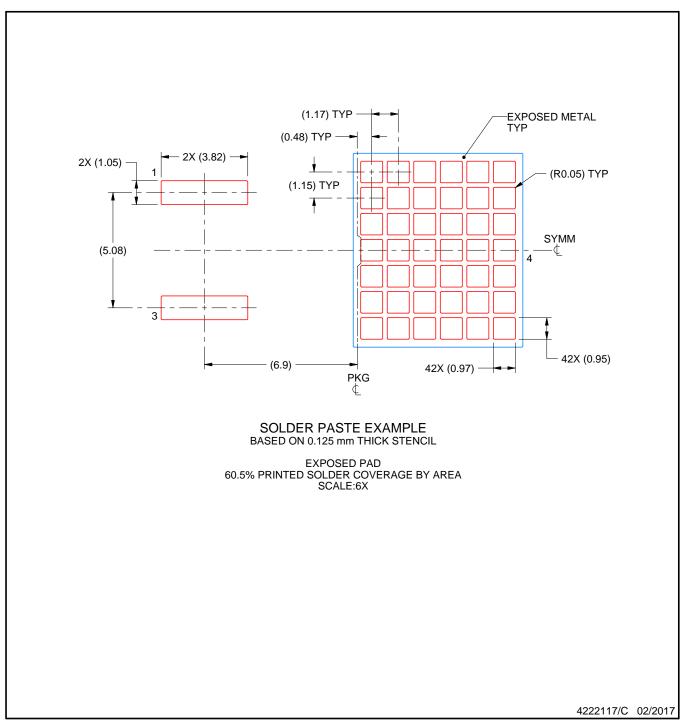


NOTES: (continued)

- 5. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature numbers SLMA002(www.ti.com/lit/slma004) and SLMA004 (www.ti.com/lit/slma004).
- 6. Vias are optional depending on application, refer to device data sheet. It is recommended that vias under paste be filled, plugged or tented.



TO-263



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

  8. Board assembly site may have different recommendations for stencil design.



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